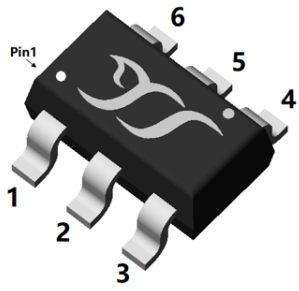
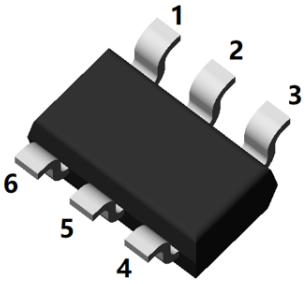
N-Channel Enhancement Mode Field Effect Transistor

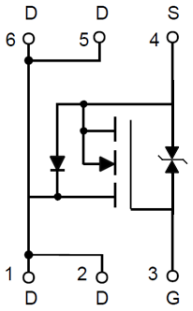


Top View



Bottom View

SOT-23-6L



Product Summary

- V_{DS} 30V
- I_D 1.4A
- $R_{DS(ON)}$(at V_{GS}=4.5V) ＜260mΩ
- $R_{DS(ON)}$(at V_{GS}=2.5V) ＜400mΩ
- ESD Protected Up to 3KV(HBM)

General Description

- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface:TTL/CMOS

■ Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V_{DS}	-	30	V
Gate-source Voltage			V_{GS}	-10	10	
Continuous Drain Current (Note 1,2)	Steady-State	T_A=25℃,V_{GS}=10V	I_D	-	1.4	A
		T_A=100℃,V_{GS}=10V		-	0.9	
Pulsed Drain Current	T_A=25℃,t_p≤10μs		I_{DM}	-	6	
Maximum Body-Diode Continuous Current	T_A=25℃		I_S		1	
Total Power Dissipation (Note 1,2)	Steady-State	T_A=25℃	P_D	-	1	W
		T_A=100℃		-	0.4	
Junction and Storage Temperature Range			T_J ,T_{STG}	-55	150	℃

■Thermal Resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	125	℃/W

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJJ260N03AK	F2	260AJ	3000	30000	120000	7“ reel

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA,Tj=25℃	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V,Tj=25℃	-	-	1	μA
		V_{DS}=30V,V_{GS}=0V,Tj=150℃	-	-	100	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±10V,V_{DS}=0V,Tj=25℃	-	-	±10	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA,Tj=25℃	0.45	0.75	1	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=4.5V,I_D=1.4A,Tj=25℃	-	205	260	mΩ
		V_{GS}=2.5V,I_D=0.7A,Tj=25℃	-	240	400	mΩ
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V,Tj=25℃	-	0.86	1.2	V
Gate Resistance	R_G	f=1MHz,Tj=25℃	-	5	-	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHz,Tj=25℃	-	58	-	pF
Output Capacitance	C_{oss}		-	9.8	-	
Reverse Transfer Capacitance	C_{rss}		-	5.1	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=4.5V,V_{DS}=15V,I_D=1.4A,Tj=25℃	-	0.9	-	nC
Gate-Source Charge	Q_{gs}		-	0.2	-	
Gate-Drain Charge	Q_{gd}		-	0.3	-	
Reverse Recovery Charge	Q_{rr}	I_F=1.4A,di/dt=100A/μs,V_{GS}=0V,V_R=15V, Tj=25℃	-	5.3	-	nC
Reverse Recovery Time	t_{rr}		-	16	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=4.5V,V_{DS}=15V,I_D=1.4A, R_{GEN}=3Ω,Tj=25℃	-	3.7	-	ns
Turn-on Rise Time	t_r		-	5.9	-	
Turn-off Delay Time	$t_{D(off)}$		-	10.4	-	
Turn-off Fall Time	t_f		-	4	-	

Note：

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in^2 pad of 2oz. Copper, in the still air environment with T_A=25℃.The maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

■Typical Electrical and Thermal Characteristics Diagrams

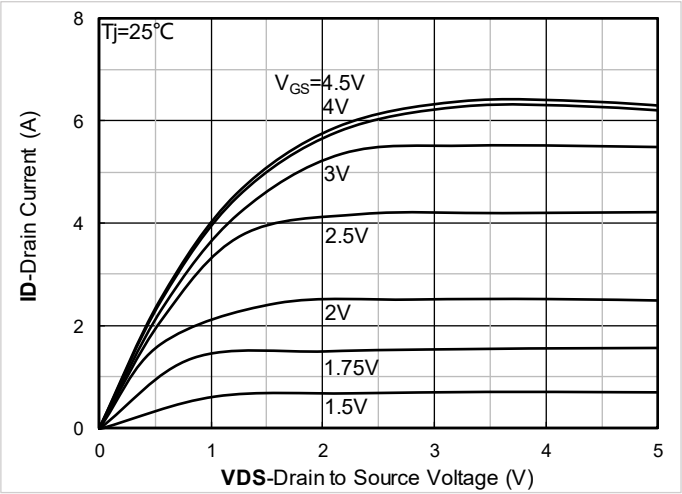


Figure 1. Output Characteristics; typical values

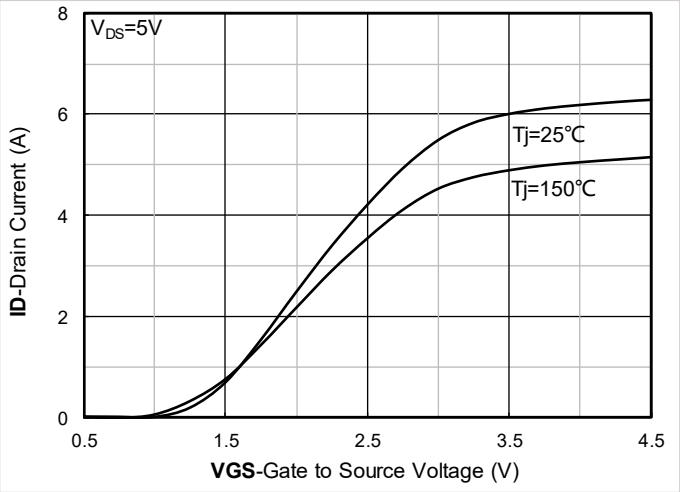


Figure 2. Transfer Characteristics; typical values

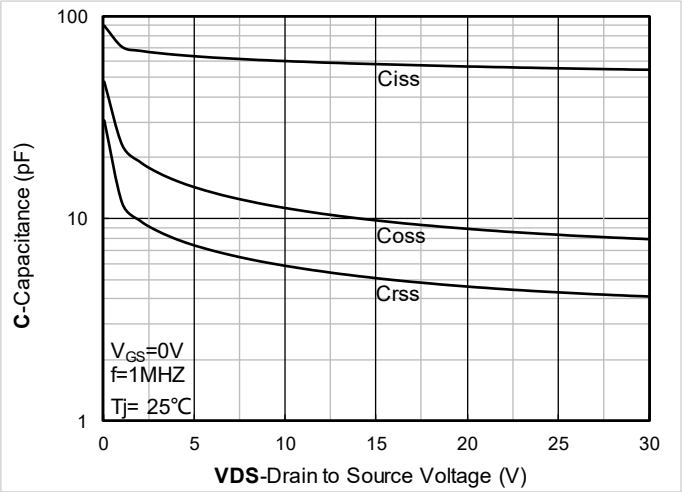


Figure 3. Capacitance Characteristics; typical values

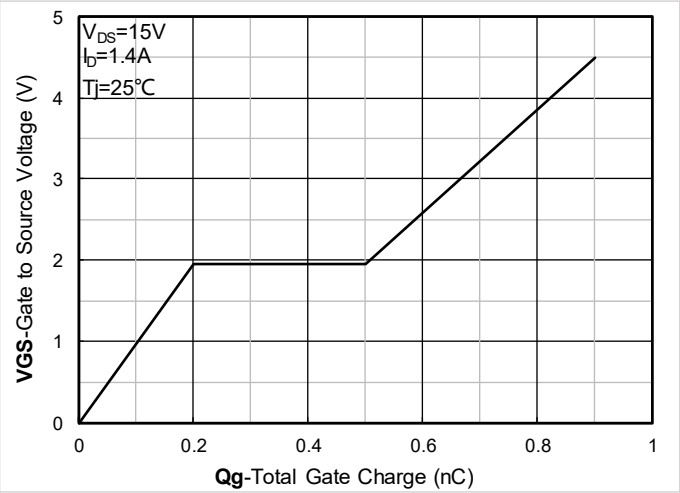


Figure 4. Gate Charge; typical values

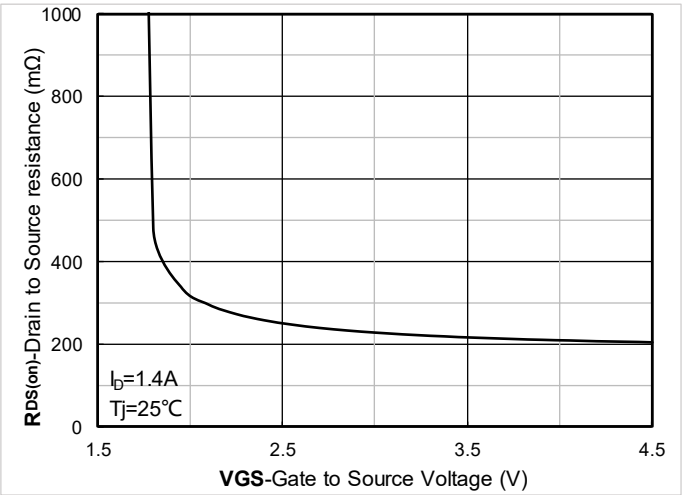


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

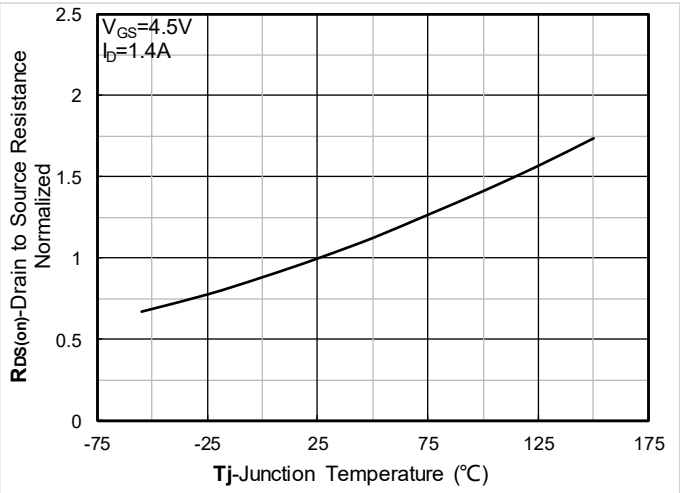


Figure 6. Normalized On-Resistance

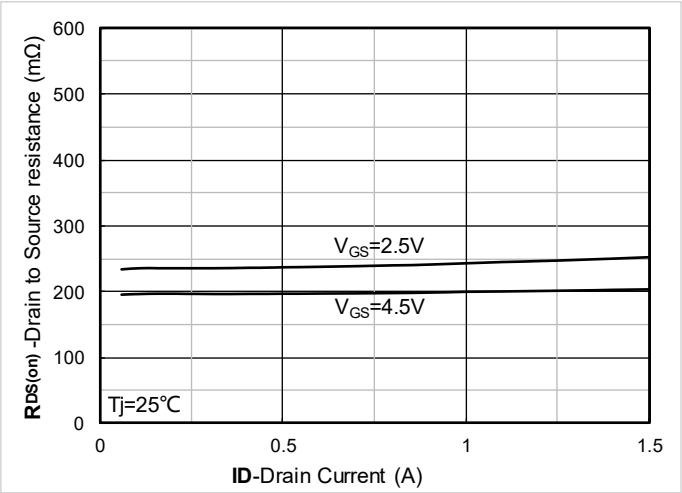


Figure 7. $R_{DS(on)}$ vs. Drain Current; typical values

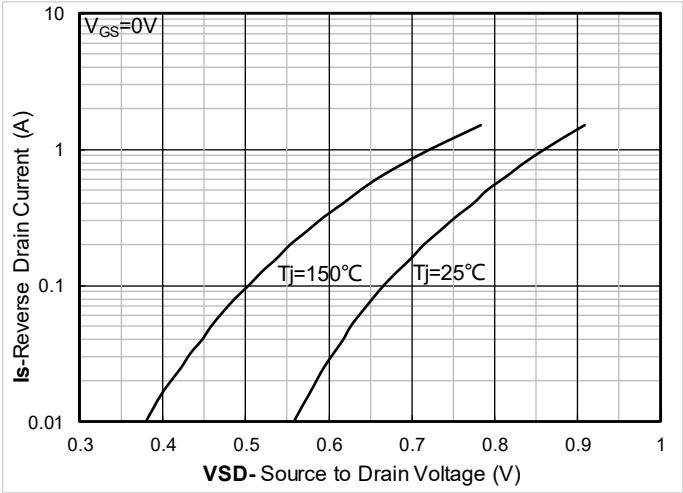


Figure 8. Forward characteristics of reverse diode; typical values

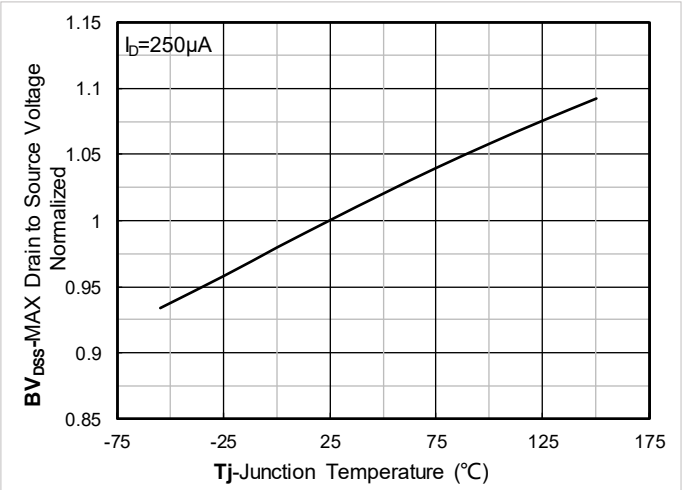


Figure 9. Normalized breakdown voltage

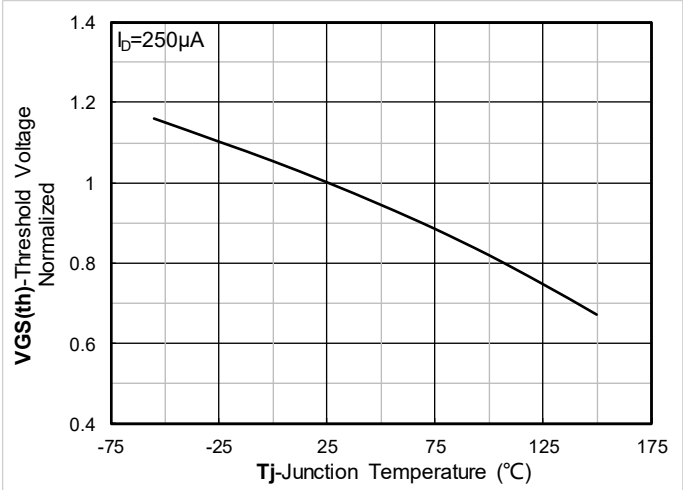


Figure 10. Normalized Threshold voltage

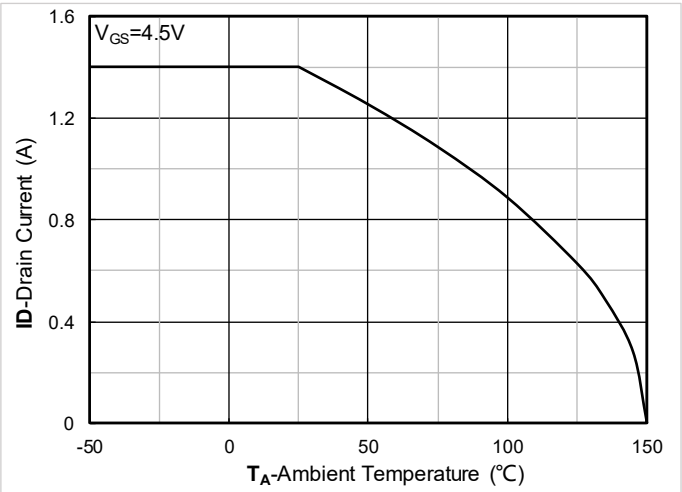


Figure 11. Current dissipation

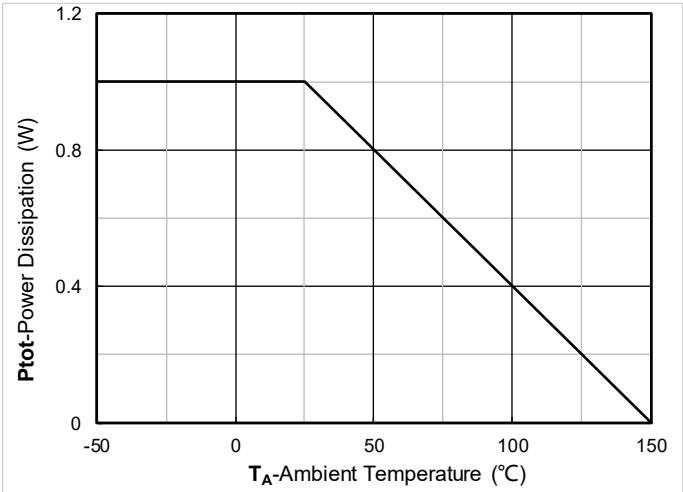


Figure 12. Power dissipation

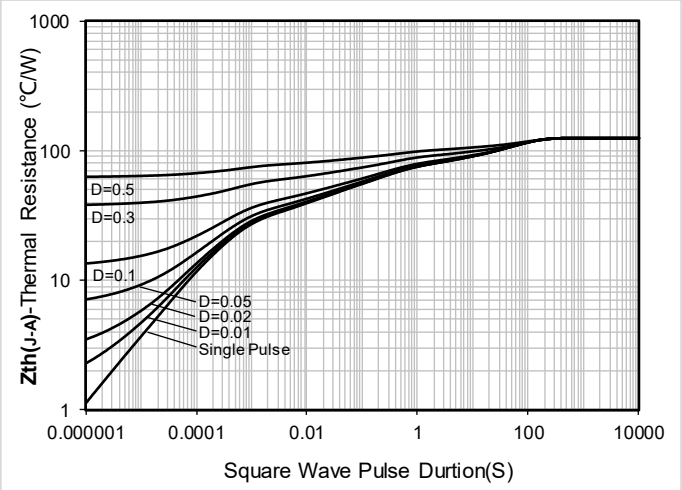


Figure 13. Maximum Transient Thermal Impedance

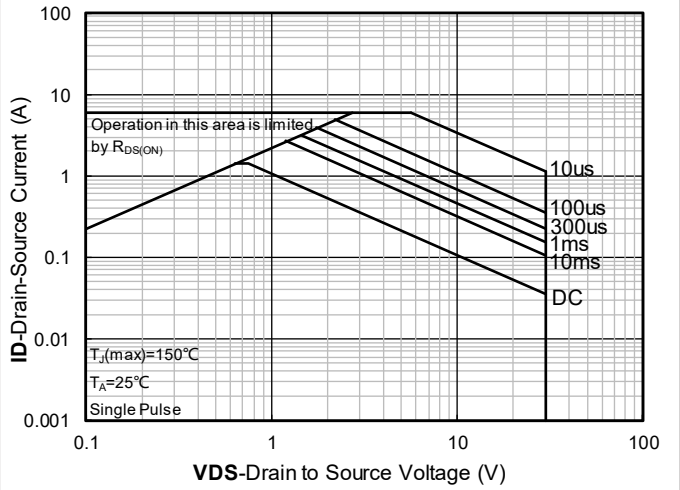


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

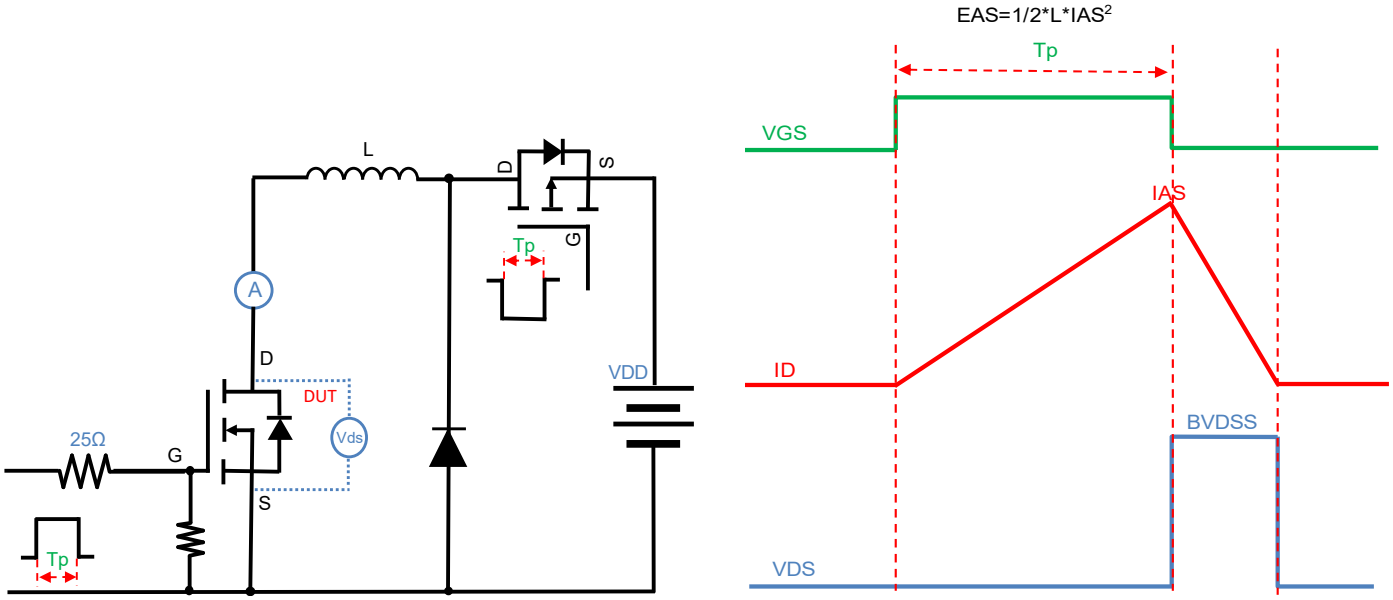


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

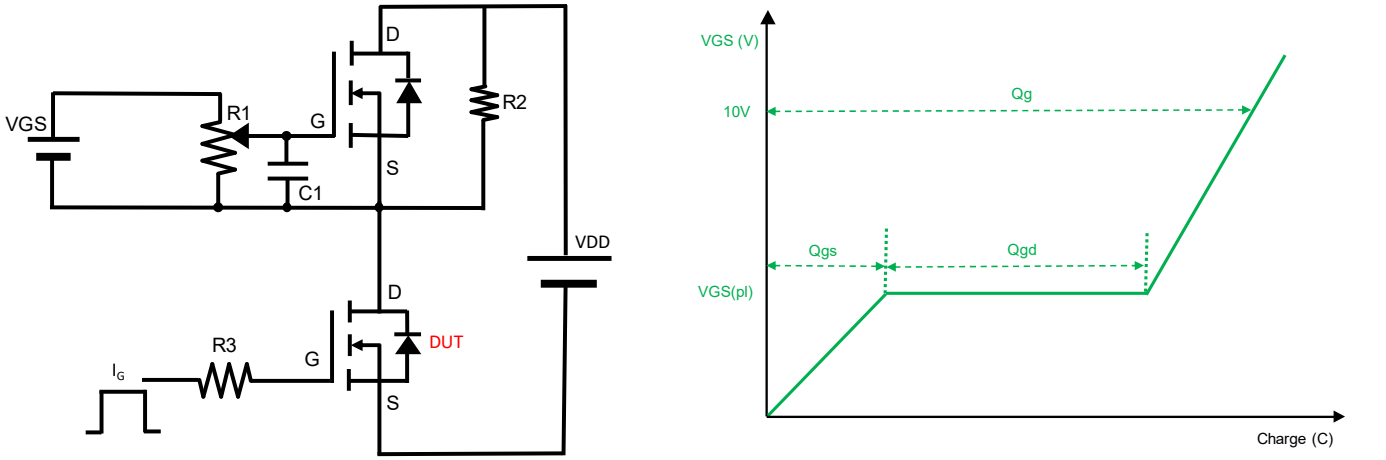


Figure B. Gate Charge Test Circuit & Waveform

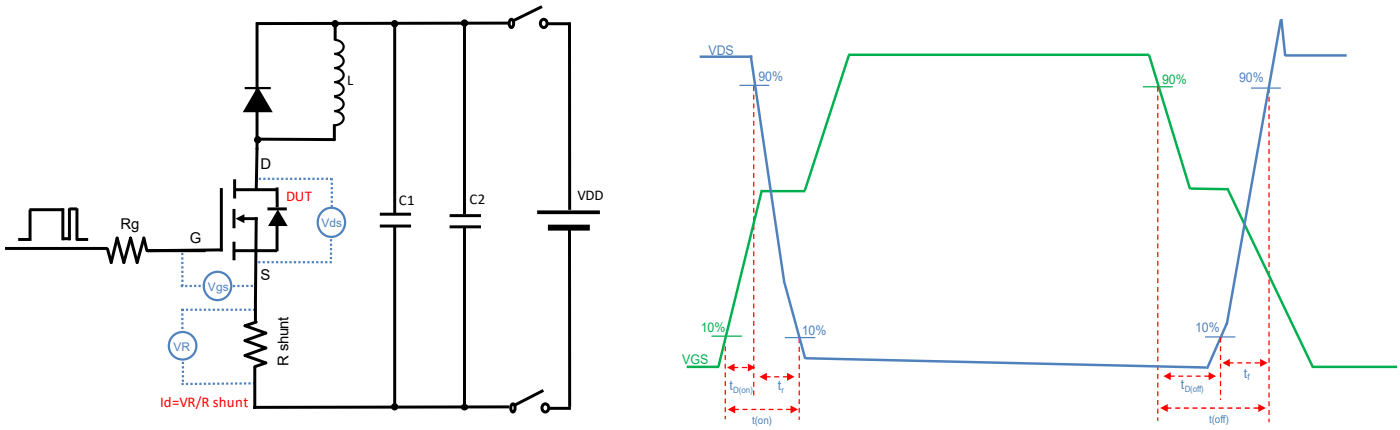


Figure C. Resistive Switching Test Circuit & Waveform

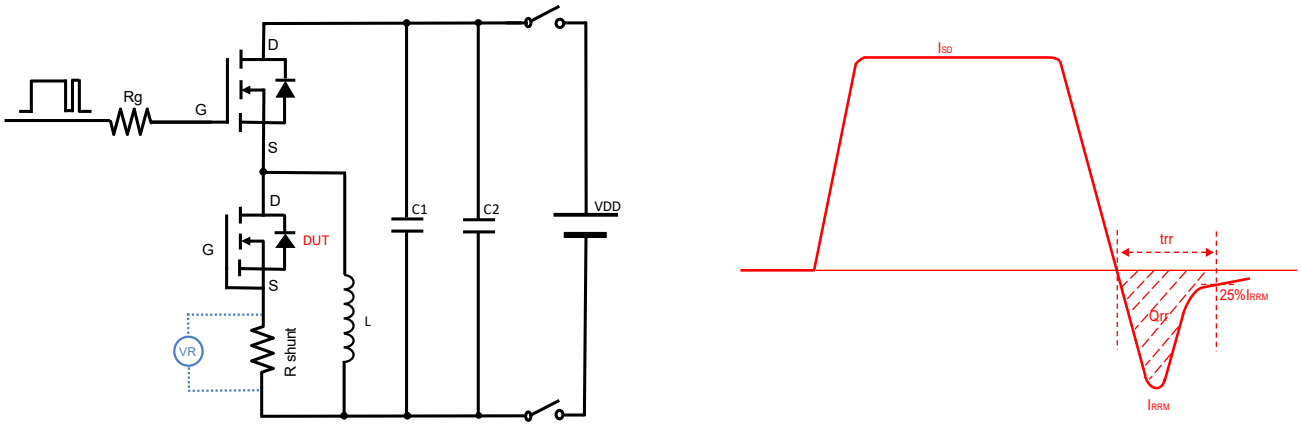
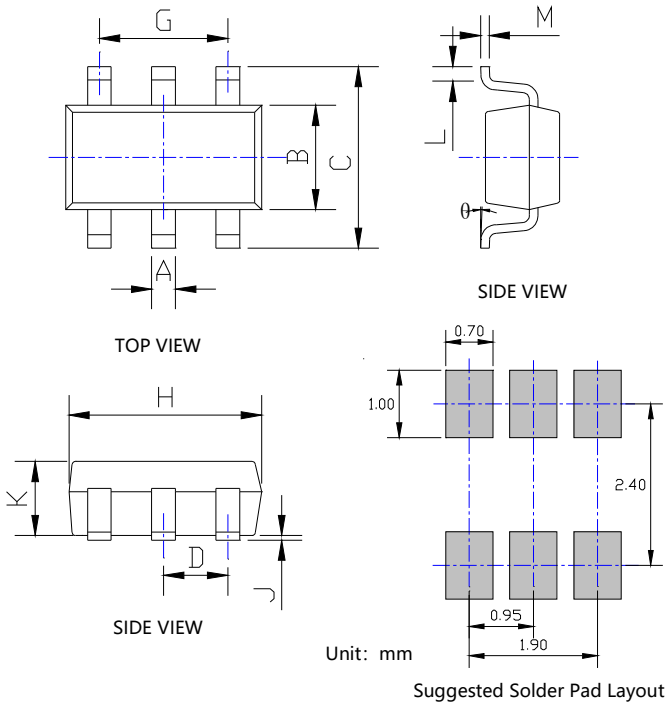


Figure D. Diode Recovery Test Circuit & Waveform

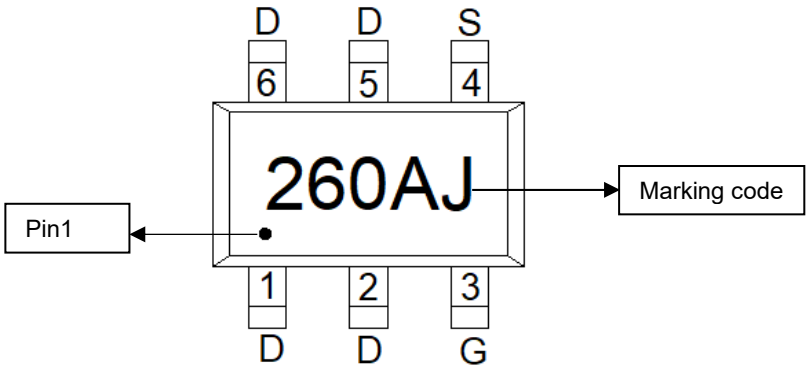
■ SOT-23-6L Package information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D	0.037BSC		0.950BSC	
G	0.075BSC		1.900BSC	
H	0.111	0.119	2.820	3.020
J	0.000	0.004	0.000	0.100
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
θ	0°	8°	0°	8°

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:+/-0.05mm.
3.The pad layout is for reference purposes only.

■ Marking Information



Note：
1. All marking is at middle of the product body
2. All marking is in laser printing
3. 260AJ is marking code
4. Body color: Black

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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